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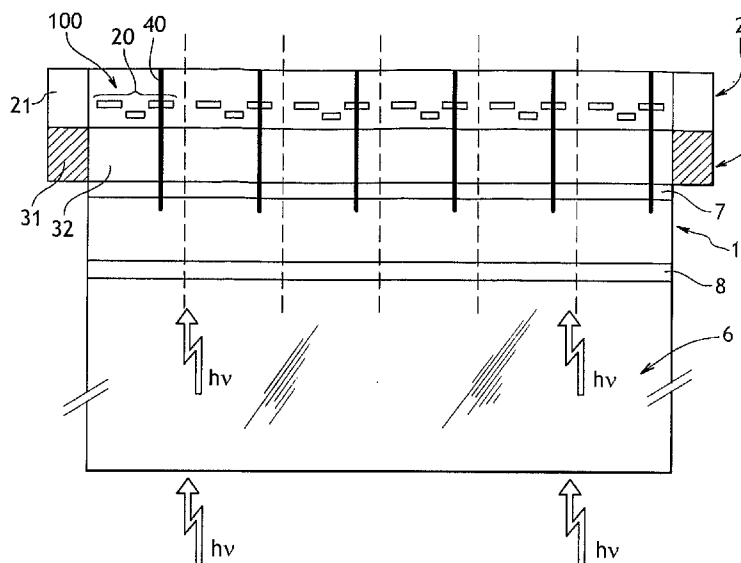
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(54) Title: PHOTODETECTING DEVICE



(57) Abstract: Method of manufacturing a photodetecting device, characterized in that it comprises the following steps: (a) providing a first wafer (I) comprising a photosensitive layer (1) made of a material chosen from semiconductor materials, and a second wafer (II) comprising a circuit layer (2) including electronic components, one of the photosensitive layer (1) and the circuit layer (2) being covered by a field isolation layer (3); (b) bonding the first wafer (I) and the second wafer (II) so as to form a structure comprising successively the circuit layer (2), the field isolation layer (3) and the photosensitive layer (1); (c) forming electrically conductive via (40) so as to electrically connect the photosensitive layer (1) to inputs of some electronic components of the circuit layer (2).

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